

In the Claims

Please amend Claim 1 as follows:

1. (Amended) An electrostatic discharge protection device consisting of:

a p-well region in a semiconductor substrate;

an n+ region in said p-well region wherein said n+
5 region is connected to a first voltage supply;

an n-well region in said p-well region wherein said n+
region is spaced from said n-well region a distance such
that a depletion region extends therebetween during normal
operation; and

10 a p+ region in said n-well region wherein said p+
region is connected to a second voltage supply of greater
value than said first voltage supply during said normal
operation wherein current is conducted through said n+
region to said p+ region during an electrostatic discharge
15 event.

Please amend Claim 8 as follows:

8. (Amended) An electrostatic discharge protection device

consisting of:

a p-well region in a semiconductor substrate;

an n+ region in said p-well region wherein said n+

5 region is connected to a first voltage supply;

an n-well region in said p-well region wherein said n+
region is spaced from said n-well region a distance such
that a depletion region extends therebetween during normal
operation and wherein said distance between said n+ region

10 and said n-well region is between about 0.2 microns and 1.0
microns; and

a p+ region in said n-well region wherein said p+
region is connected to a second voltage supply of greater
value than said first voltage supply during said normal

15 operation wherein current is conducted through said n+
region to said p+ region during an electrostatic discharge
event.

Please amend Claim 14 as follows:

14. (Amended) An electrostatic discharge protection circuit
on an integrated circuit device, said protection circuit
consisting of:

a ground pad connected to an external ground reference
and to a p+ region in a p-well in a substrate;

5 a first voltage supply pad connected to an external
first voltage supply and to an n+ region in said p-well;
and

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cont*
10 a second voltage supply pad connected to an external
second voltage supply of greater value than said external
first voltage supply during normal operation and to a p+
region in an n-well region in said p-well region wherein
said n+ region is spaced from said n-well region a distance
such that a depletion region extends therebetween during
said normal operation, and wherein current is conducted
15 through said external second voltage supply pad to said
external first voltage supply pad during an electrostatic
discharge event.

REMARKS

Examiner O. Nadav is thanked for the thorough examination
and search of the subject Patent Application. Claims 1, 8, and
14 have been amended.